

MATERIALS AND GAS CHEMISTRIES FOR PROCESSING SYSTEMS

ABSTRACT

A plasma processing system for processing a substrate, is disclosed. The 5 plasma processing system includes a single chamber, substantially azimuthally symmetric plasma processing chamber within which a plasma is both ignited and sustained for the processing. The plasma processing chamber has no separate plasma generation chamber. The plasma processing chamber has an upper end and a lower end. The plasma processing chamber includes a material that does not substantially 10 react with the reactive gas chemistries that are delivered into the plasma processing chamber. In addition, the reactant gases that are flown into the plasma processing chamber are disclosed.

000102347444609